



# Bipolar PNP Bare Die – BTP6058

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## Part Description

The BTP6058 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

## Key Parameters:

- VCBO = -30V
- VCEO = -20V
- VEBO = -6V
- hFE = 82-390 @ VCE = -2V, IC = -0.5A
- VCE(Sat) = -1V @ IC = -4A, IB = -100mA
- fT = 120 MHz @ VCE = -6V, IE = 0A
- COBO = 60pF @ VCB = -20V

## Features

Low VCE(sat). Designed to provide performance equivalent to Panasonic 2SD965 or ROHM 2SB1412

## Die Size (Unawn)

1300 $\mu$ m X 1300 $\mu$ m, 51 Mils X 51 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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